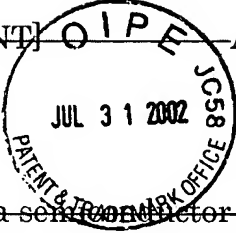


[NAME OF DOCUMENT]  ABSTRACT

[ABSTRACT] —

[OBJECT] —

~~An object is to provide a semiconductor device and a method for manufacturing the same that is excellent in reduction of leak current caused by the short-channel effect.~~

[MEANS FOR SOLUTION]

A field effect transistor formed on a SOI substrate is equipped with a gate (102) formed on a substrate, a source (103) and a drain (104) each spaced a specified distance from a crystal region below the gate, a first extension region (110) that extends in a channel formed between the source and an area below the gate, and a second extension region (111) that extends in a channel formed between the drain and an area below the gate, wherein junction depths ( $X_s$ ,  $X_d$ ) of the first and second extension regions is formed shallower than junction depths ( $X_t$ ) of the source region (103) and the drain region (104).

[SELECTED FIGURE] — Fig. 1